



1. Description

SS036N10MS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V _{DSS}	100	V
I _D	120	A
R _{DS(on).typ}	3.0	mΩ

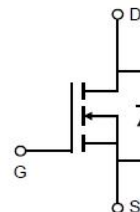
FEATURES

- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 3.6\text{m}\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

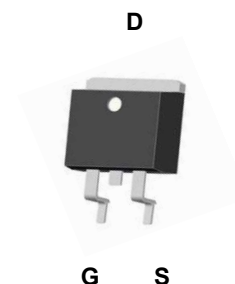
APPLICATIONS

- Switching applications
- Motor drivers

Schematic Diagram



TO-263-2L top view



ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS036N10MS	TO-263	SS036N10MS	Reel